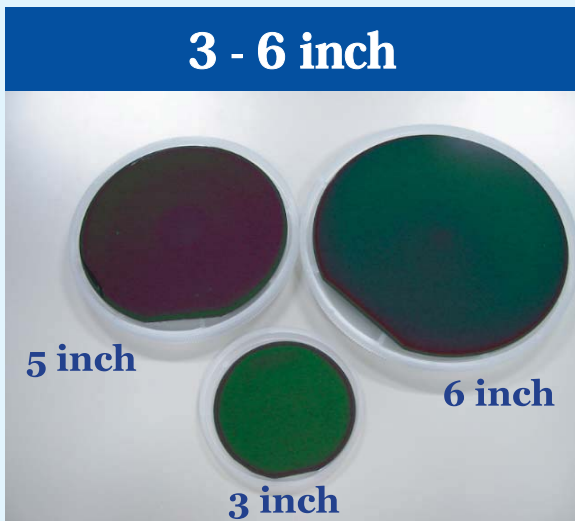
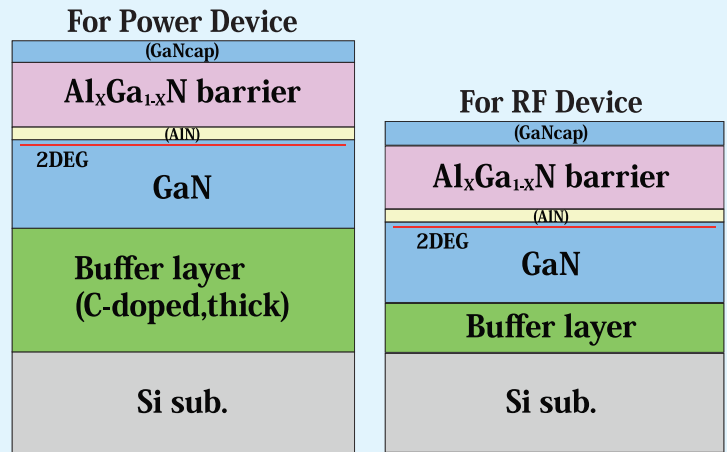


# GaN Epitaxial Wafers

## ● For AlGaN/GaN HEMT on Silicon



## Layer structure



## ● Sheet resistance & Mobility (typical values)



- **Sheet resistance**  
Average : 440ohm/sq.  
Variation : 6.9%

- **Mobility**  
Average : 2,128cm<sup>2</sup>/Vs  
Variation : 4.75%

